

# SANYO Semiconductors DATA SHEET

### N-Channel Silicon MOSFET

# **CPH6414** — General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- 4V drive.

# **Specifications**

### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	20	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm <sup>2</sup> X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			1.1
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS= ±16V, VDS=0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	3.1	4.5		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=3A, VGS=10V		37	48	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.5A, V <sub>GS</sub> =4V		63	88	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		460		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		95		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		75		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		11		ns
Rise Time	tr	See specified Test Circuit.		12		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		31		ns
Fall Time	tf	See specified Test Circuit.		18		ns

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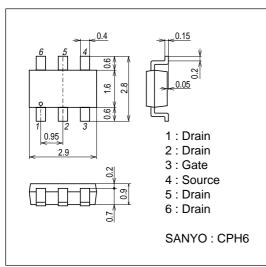
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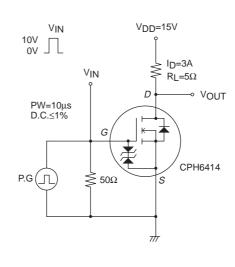
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	1 01111
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		8.5		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		1.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		1.3		nC
Diode Forward Voltage	VSD	IS=5A, VGS=0V		0.86	1.2	V

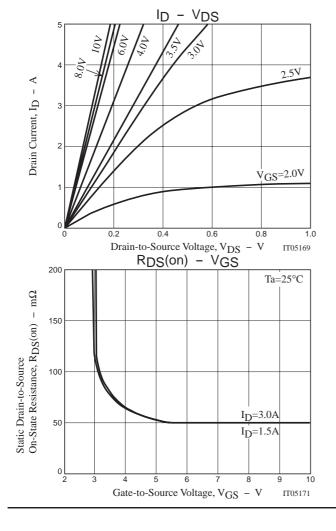
## **Package Dimensions**

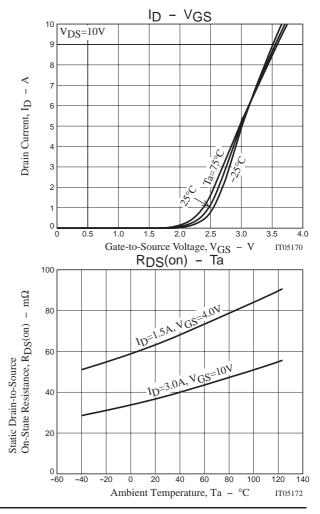
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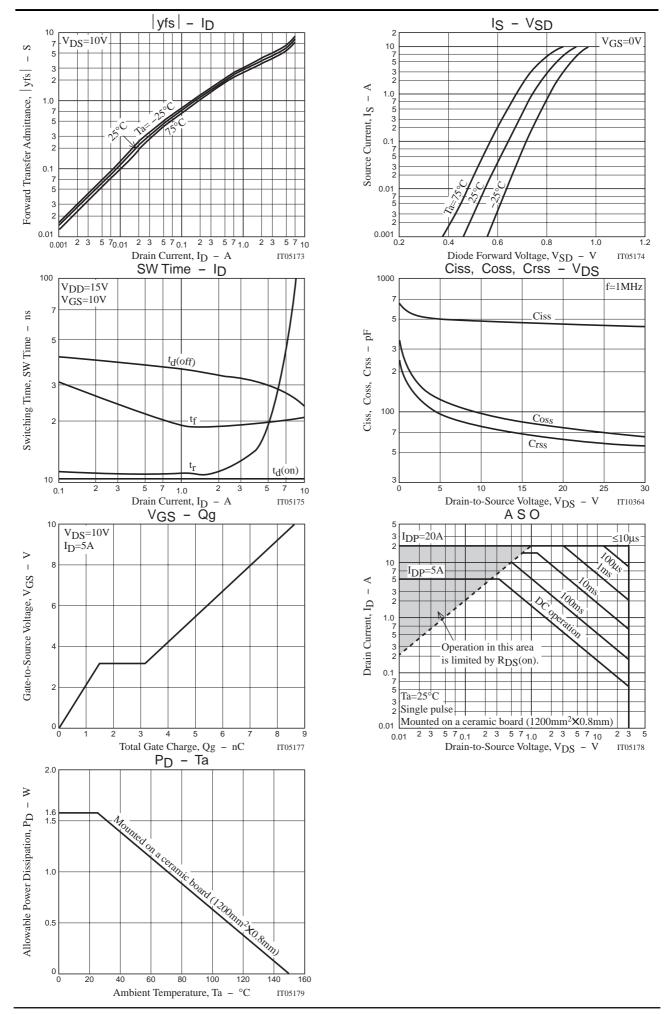


# **Switching Time Test Circuit**









Note on usage: Since the CPH6414 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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